

The UAA3536 is a low-power GSM triple-band transceiver based on the N-ZIF (Near-Zero Intermediate Frequency) RF architecture. The UAA3536 is a GSM900/1800/1900 GPRS class 12-capable single-chip RF solution, with edge 4RX capabilities.

UAA3536

Low-power GSM/GPRS/EDGE triple-band Near-Zero IF transceiver

The UAA3536 N-ZIF architecture, targeted at triple-band GSM900/1800/1900 GPRS Class 12 handsets with EDGE receiving capability, integrates many different features including a high dynamic range IF channel filter, a low-noise amplifier (LNA) with image rejecting front end, Fractional N frequency synthesizers and a transmit offset loop with integrated filters. It provides a definitive advantage compared to Zero-IF (ZIF) solutions in terms of immunity to interference, RF development cost, time and manufacturing.

This new architecture removes a conversion step between the RF and the baseband. Compared to other architectures, N-ZIF allows to remove the costly external IF channel filter. With the full integration of Rx VCO and fractional N synthesizer, it is a major innovation step towards higher integration within RF ICs.

Availability

The UAA3536 single-chip RF transceiver is about to sample, with mass production expected by mid 2001. It is manufactured in Philips Semiconductors' advanced QUBIC 3 BiCMOS process and is packaged in an HVQFN 40 package.

The UAA3536 interfaces with current and future Philips Semiconductors' products and will be at the heart of the company's chipset offerings. The IC will be fully compatible with OneC Baseband family, the new CGY2015 power amplifier and the PCF5060x power management unit platform.

Key Features

- Triple-band RF solution for GSM900/1800/1900 cellular phone systems
- Integrated on-chip data services: GPRS Class 12 (4RX-4TX) with data rate up to 57.6kB/s and EDGE (4RX) with data rate up to 237kb/s
- Low-cost N-ZIF architecture because of the low external components count
- Excellent power consumption performance
- Low noise and wide dynamic range Near Zero IF receiver:
 - More than 35-dB on-chip image rejection in receive
 - More than 84-dB gain control range in receive
- Integrated IF channel filter
- Integrated TX low pass filters
- High precision I&Q modulator
- Multi-Band Tx modulation loop architecture including offset mixer and phase-frequency detector
- Fully integrated fractional N RF synthesizer with AFC control capability
- Fully integrated RF VCO with integrated supply regulator
- Semi integrated reference oscillator with integrated supply regulator
- Fully differential design minimizing cross-talk and spurs
- Functional down to 2.6 V and up to 3.6 V
- 3-wire serial bus interface
- HVQFN40 package

Let's make things better.



PHILIPS

UAA3536

Key Blocks

RF Receiver

The receiver front-end converts the aerial RF signal from EGSM (925 - 960 MHz), DCS (1805 - 1880 MHz) or PCS (1930 - 1990 MHz) bands down to a Near-Zero intermediate frequency (IF). The first stages are symmetrical low noise amplifiers (LNAs), followed by an I&Q down-mixer. The I&Q down-mixer consists of two mixers in parallel but is driven by quadrature out of phase LO signals. The In phase (I) and Quadrature phase (Q) IF signals are then low pass filtered to provide protection from high frequency offset interferers. The Near-Zero IF I and Q signals are then fed into the channel filter.

Channel filter and AGC

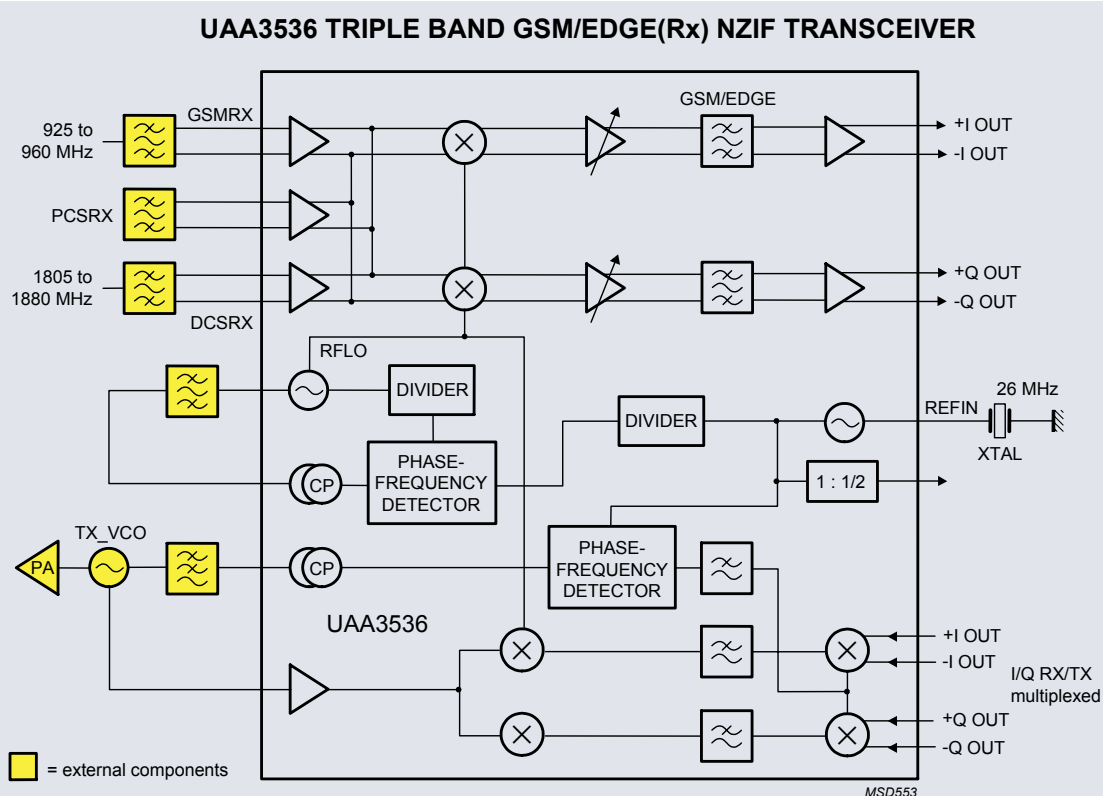
The front-end near Zero IF I and Q outputs enters the integrated bandpass channel filter. Being filtered the Near-Zero IF I and Q are further amplified with provision for 68dB Automatic Gain Control (AGC) and DC offset compensation. The IF channel is able to program the bandwidth between GSM and EDGE, to allow optimum performance in each mode.

IQ modulator

I and Q baseband signals are applied to the IQ modulator that shifts the modulation spectrum up to the transmit IF. It is designed for low harmonic distortion, low carrier leakage and high image rejection to harmonic distortion, low carrier leakage and high image rejection to keep the phase error as small as possible. The modulator is loaded at its IF output by an integrated low pass filter that suppress unwanted spurs prior to get into the phase detector.

Transmit modulation loop

The analog transmit modulation loop is composed by on-chip offset mixer, a phase/frequency detector working in and by off-chip loop filter and transmit VCO. The analog PLL copies the modulation to the off-chip transmit VCO and acts as a tracking filter. A PLL of at least third order is required to meet noise requirements at 20 MHz offset from carrier. The PLL bandwidth is optimized in order to keep a low dynamic phase error and to minimize the acquisition time.



RF and IF LO sections

The RF LO input covering the 1788 to 2002 MHz bandwidth is connected to an internal RF VCO. The RF LO section includes the LO buffering for the RF PLL, a divider by two or one for GSM and DCS/PCS respectively which drives a quadrature generation network for use in the RX IQ down-mixer or the transmit modulation loop offset mixer. A new TX architecture does not require any IF LO.

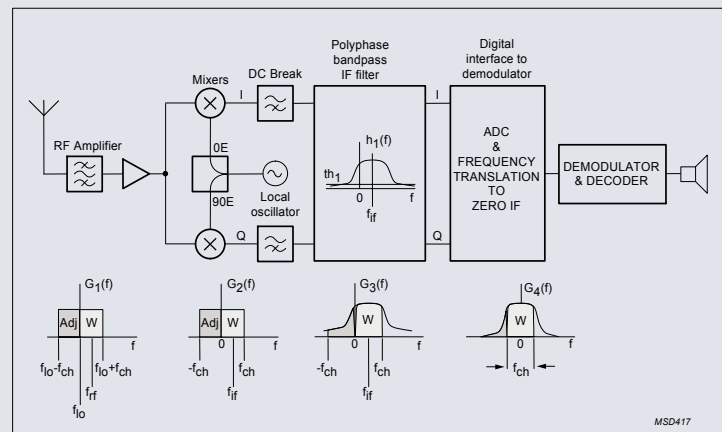
Dual PLL

A high performance RF fractional N PLL is included on chip which allows to synthesize the frequencies of the RF VCO on chip. Very low close-in phase noise is achieved allowing to widen the PLL loop bandwidth for shorter settling time, providing GPRS Class 12 capabilities in terms of hardware. The charge pump circuit has very low leakage current, in the nA range, so that the spurs are hardly detectable.

The programmable 'main' dividers are controlled by a Sigma Delta modulus divider. Their phase of the signal divided is then compared into a digital phase/frequency detector (PFD) to that of the 26MHz reference clock signal. The phase error information is fed back to the VCO via the charge pump circuit that 'sinks' into or 'sources' current from the loop filter capacitor, changing the VCO frequency such that the loop gets finally 'phase locked'.

N-ZIF architecture

The N-ZIF architecture integrates many different features including a high dynamic range IF channel filter, a low-noise amplifier (LNA) with image rejecting front end, fractional N frequency synthesizers and a transmit offset loop with integrated filters. It provides a definitive advantage compared to Zero-IF (ZIF) solutions in terms of immunity to interference, RF development cost, time and manufacturing. In addition to providing simplified signal processing for GSM applications, the high integration level it achieves provides significant cost and size reductions.



Near-Zero IF architecture - it eliminates the need for an external SAW filter and also prevents DC errors by allowing a DC break to be inserted into the IF path. The filters that are required are non-critical and can easily be implemented on-chip

Future

The UAA3536 joins a family of products that will pave the way for the continued evolution of GSM and the progression to 3G. Philips Semiconductors' next product offering will be focussed on 3G, with an even higher level of integration and new multimedia features to keep the company at the leading edge of cellular technology.

In addition to providing enhanced data rate capabilities, Philips Semiconductors' next generation of chipsets will integrate new capabilities such as Bluetooth, MP3 (Moving Picture Experts Group Layer-3 Audio) and GPS (Global Positioning System), and will directly address 3G standards such as UMTS (Universal mobile Telecommunications System) and W-CDMA (Wide-band Code Division Multiple Access).

Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 3 Figtree Drive, HOMEBUSH, NSW 2140,
Tel. +61 2 9704 8141, Fax. +61 2 9704 8139

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,
Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

Belgium: see The Netherlands

Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoprojekt, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 68 9211, Fax. +359 2 68 9102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Sydhavnsgade 23, 1780 COPENHAGEN V,
Tel. +45 33 29 3333, Fax. +45 33 29 3905

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615 800, Fax. +358 9 6158 0920

France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex,
Tel. +33 1 4099 6161, Fax. +33 1 4099 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 2353 60, Fax. +49 40 2353 6300

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor,
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,
Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: PT Philips Development Corporation, Semiconductors Division,
Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,
Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Via Casati, 23 - 20052 MONZA (MI),
Tel. +39 039 203 6838, Fax +39 039 203 6800

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,
TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5057

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Pakistan: see Singapore

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Al.Jerozolimskie 195 B, 02-222 WARSAW,
Tel. +48 22 5710 000, Fax. +48 22 5710 001

Portugal: see Spain

Romania: see Italy

Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 319762,
Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria

Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 58088 Newville 2114,
Tel. +27 11 471 5401, Fax. +27 11 471 5398

South America: Al. Vicente Pinzon, 173, 6th floor,
04547-130 Sˆ O PAULO, SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 821 2382

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 93 301 6312, Fax. +34 93 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
Tel. +46 8 5985 2000, Fax. +46 8 5985 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,
Tel. +41 1 488 2741 Fax. +41 1 488 3263

Taiwan: Philips Semiconductors, 5F, No. 96, Chien Kuo N. Rd., Sec. 1,
TAIPEI, Taiwan Tel. +886 2 2134 2451, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
60/14 MOO 11, Bangna Trad Road KM. 3, Bagna, BANGKOK 10260,
Tel. +66 2 361 7910, Fax. +66 2 398 3447

Turkey: Yukari Dudullu, Org. San. Blg., 2.Cad. Nr. 28 81260 Umranıye,
ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 208 730 5000, Fax. +44 208 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,
Tel. +381 11 3341 299, Fax. +381 11 3342 553

For all other countries apply to: Philips Semiconductors,
Marketing Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN,
The Netherlands, Fax. +31 40 27 24825

Internet: <http://www.semiconductors.philips.com>

© Philips Electronics N.V. 2000

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Date of release: September, 2000 - Printed in the Netherlands

Document order: 939775007501

Let's make things better.



PHILIPS